

## PATENT APPLICATION

#16/c 40 6/1/03

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Li et al.	)	I hereby certify that this paper is being deposited with			
Serial No.:	09/662,682	)	the United States Postal Service as FIRST-CLASS main an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450			
Filed:	September 15, 2000	)	on this date.	_ •	, <u></u>	
For:	METAL-ASSISTED CHEMIC ETCH POROUS SILICON FORMATION METHOD	) :AL) ) )	May 23,2003 Date F-CLASS.WCM Appr. February 20, 1998	CLA B, Registration No Attorney for A	_	
Art Unit:	1765	)		P/		
Examiner:	Vinh, Lan	)		Mar	CEIL	
	AMENDME	MAY 29 2003				
					( )_	

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action mailed December 26, 2002, please amend the above-identified application as follows: